

In the Claims:

1 1. (currently amended) A method of manufacturing single-
2 crystal semiconductor blocks, wherein small-diameter
3 single-crystal semiconductor blocks ~~[[2a]]~~ of a relatively
4 small diameter for slicing off single-crystal semiconductor
5 wafers of a relatively small diameter desired by users are
6 cut out from a large-diameter single-crystal semiconductor
7 block ~~[[1a]]~~ of a relatively large diameter.

1 2. (original) The method of manufacturing single-crystal
2 semiconductor blocks according to claim 1, wherein said
3 semiconductor is a III-V group compound semiconductor.

1 3. (original) The method of manufacturing single-crystal
2 semiconductor blocks according to claim 1, wherein said
3 large-diameter single-crystal semiconductor block has a
4 thickness of at least 10 mm.

1 4. (original) The method of manufacturing single-crystal
2 semiconductor blocks according to claim 1, wherein said
3 small-diameter single-crystal semiconductor blocks are cut
4 out by any of an electric discharge machining method, a
5 wire saw method, a grinding method by means of a
6 cylindrical core, and a band saw method.

1 5. (currently amended) The method of manufacturing single-
2 crystal semiconductor blocks according to claim 1, wherein
3 at least four said ~~small-scale~~ small-diameter
4 single-crystal semiconductor blocks having a diameter of at
5 least 2 inches are cut out from said ~~large-scale~~
6 large-diameter single-crystal semiconductor block having a
7 diameter of at least 5 inches.

1 6. (currently amended) The method of manufacturing
2 single-crystal semiconductor blocks according to claim 1,
3 wherein a total cross-sectional area of a plurality of said
4 small-diameter single-crystal semiconductor blocks cut out
5 from said ~~large-scale~~ large-diameter single-crystal
6 semiconductor block corresponds to at least 50% of a
7 cross-sectional area of said ~~large-scale~~ large-diameter
8 single-crystal semiconductor block.

1 7. (original) The method of manufacturing single-crystal
2 semiconductor blocks according to claim 1, wherein
3 defective parts included in any cross-sectional area of
4 said large-diameter single-crystal semiconductor block
5 correspond to at most 65% of said cross-sectional area.

1 8. (original) The method of manufacturing single-crystal
2 semiconductor blocks according to claim 1, wherein each of
3 said small-diameter single-crystal semiconductor blocks is
4 formed to have at least any of an orientation flat, an

5 index flat, and a notch for easy determination of its
6 crystal orientation.

[AMENDMENT FOLLOWS ON NEXT PAGE]

USPS EXPRESS MAIL
EV 636 851 726 US
OCT 03 2005